

Wojciech Linhart

List of Publications by Year in descending order

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41
papers

1,307
citations

430874

18
h-index

345221

36
g-index

41
all docs

41
docs citations

41
times ranked

1765
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 1 | Nesting-like band gap in bismuth sulfide Bi_2S_3 . Journal of Materials Chemistry C, 2021, 9, 13733-13738. | 5.5 | 18 |
| 2 | Optical properties and dynamics of excitons in Ga(Sb, Bi)/GaSb quantum wells: evidence for a regular alloy behavior. Semiconductor Science and Technology, 2020, 35, 025024. | 2.0 | 3 |
| 3 | Sn 5s ² lone pairs and the electronic structure of tin sulphides: A photoreflectance, high-energy photoemission, and theoretical investigation. Physical Review Materials, 2020, 4, . | 2.4 | 11 |
| 4 | Temperature-dependent study of GaAs _{1-x} N _x Bi _y alloys for band-gap engineering: photoreflectance and $k \cdot \text{Å}^{-1}$ modeling. Applied Physics Express, 2020, 13, 091005. | 2.4 | 6 |
| 5 | Photoreflectance and photoinduced microwave reflectance studies of surface band bending in Mg-doped InN. Journal of Applied Physics, 2019, 126, 045712. | 2.5 | 3 |
| 6 | Mapping the composition-dependence of the energy bandgap of GaAsN _x Bi _y alloys. Applied Physics Letters, 2019, 115, 082106. | 3.3 | 7 |
| 7 | Effects of the host conduction band energy on the electronic band structure of ZnCdTeO dilute oxide alloys. Journal of Applied Physics, 2019, 126, 083106. | 2.5 | 5 |
| 8 | Nitrogen pair-induced temperature insensitivity of the band gap of GaNSb alloys. Journal Physics D: Applied Physics, 2019, 52, 045105. | 2.8 | 0 |
| 9 | Novel Type-II InAs/AlSb Core-Shell Nanowires and Their Enhanced Negative Photocurrent for Efficient Photodetection. Advanced Functional Materials, 2018, 28, 1705382. | 14.9 | 36 |
| 10 | Band gap temperature-dependence of close-space sublimation grown Sb ₂ Se ₃ by photo-reflectance. APL Materials, 2018, 6, 084901. | 5.1 | 70 |
| 11 | Band gap temperature-dependence and exciton-like state in copper antimony sulphide, CuSbS ₂ . APL Materials, 2018, 6, . | 5.1 | 14 |
| 12 | Temperature dependence of band gaps in dilute bismides. Semiconductor Science and Technology, 2018, 33, 073001. | 2.0 | 15 |
| 13 | Multicolor emission from intermediate band semiconductor ZnO _{1-x} Sex. Scientific Reports, 2017, 7, 44214. | 3.3 | 19 |
| 14 | Indium-incorporation enhancement of photoluminescence properties of Ga(In)SbBi alloys. Journal Physics D: Applied Physics, 2017, 50, 375102. | 2.8 | 8 |
| 15 | Dilute Bismide Nanowires. , 2017, , 161-176. | | 0 |
| 16 | Photoacoustic spectroscopy of absorption edge for GaAsBi/GaAs nanowires grown on Si substrate. Applied Physics Letters, 2016, 109, 182106. | 3.3 | 19 |
| 17 | Band gap reduction in InN _x Sb _{1-x} alloys: Optical absorption, $k \cdot \text{Å}^{-1}$ modeling, and density functional theory. Applied Physics Letters, 2016, 109, . | 3.3 | 9 |
| 18 | Direct Measurements of Fermi Level Pinning at the Surface of Intrinsically n-Type InGaAs Nanowires. Nano Letters, 2016, 16, 5135-5142. | 9.1 | 60 |

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 19 | Electronic and optical properties of single crystal SnS ₂ : an earth-abundant disulfide photocatalyst. Journal of Materials Chemistry A, 2016, 4, 1312-1318. | 10.3 | 246 |
| 20 | The influence of nitrogen and antimony on the optical quality of InNAs(Sb) alloys. Journal Physics D: Applied Physics, 2016, 49, 115105. | 2.8 | 7 |
| 21 | Band Gap Dependence on Cation Disorder in ZnSnN ₂ Solar Absorber. Advanced Energy Materials, 2015, 5, 1501462. | 19.5 | 96 |
| 22 | Bi flux-dependent MBE growth of GaSbBi alloys. Journal of Crystal Growth, 2015, 425, 241-244. | 1.5 | 27 |
| 23 | Optical properties of GaAsBi/GaAs quantum wells: Photoreflectance, photoluminescence and time-resolved photoluminescence study. Semiconductor Science and Technology, 2015, 30, 094005. | 2.0 | 30 |
| 24 | Bi-induced band gap reduction in epitaxial InSbBi alloys. Applied Physics Letters, 2014, 105, . | 3.3 | 48 |
| 25 | Photoreflectance spectroscopy of GaInSbBi and AlGaSbBi quaternary alloys. Applied Physics Letters, 2014, 105, . | 3.3 | 11 |
| 26 | Low- and high-energy photoluminescence from GaSb _{1-x} Bi _x with 0 < x < 0.042. Applied Physics Express, 2014, 7, 111202. | 2.4 | 30 |
| 27 | Ge interface engineering using ultra-thin La ₂ O ₃ and Y ₂ O ₃ films: A study into the effect of deposition temperature. Journal of Applied Physics, 2014, 115, . | 2.5 | 47 |
| 28 | Theoretical and experimental studies of electronic band structure for GaSb _{1-x} Bi _x in the dilute Bi regime. Journal Physics D: Applied Physics, 2014, 47, 355107. | 2.8 | 50 |
| 29 | High Bi content GaSbBi alloys. Journal of Applied Physics, 2014, 116, . | 2.5 | 70 |
| 30 | Growth, disorder, and physical properties of ZnSnN ₂ . Applied Physics Letters, 2013, 103, . | 3.3 | 111 |
| 31 | Growth and properties of GaSbBi alloys. Applied Physics Letters, 2013, 103, 142106. | 3.3 | 84 |
| 32 | Sulfur passivation of surface electrons in highly Mg-doped InN. Journal of Applied Physics, 2013, 114, 103702. | 2.5 | 3 |
| 33 | Temperature dependence of the band gap of GaSb _{1-x} Bi _x alloys with 0 < x < 0.042 determined by photoreflectance. Applied Physics Letters, 2013, 103, . | 3.3 | 46 |
| 34 | Optical absorption by dilute GaNSb alloys: Influence of N pair states. Applied Physics Letters, 2013, 103, 042110. | 3.3 | 22 |
| 35 | MBE growth and characterization of Mn-doped InN. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, . | 1.2 | 5 |
| 36 | Giant Reduction of InN Surface Electron Accumulation: Compensation of Surface Donors by Mg Dopants. Physical Review Letters, 2012, 109, 247605. | 7.8 | 20 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 37 | Epitaxial InGaN on nitridated Si(111) for photovoltaic applications. , 2012, , . | | 1 |
| 38 | Structural, electrical and optical characterization of MOCVD grown In-rich InGaN layers. Journal of Crystal Growth, 2012, 358, 51-56. | 1.5 | 6 |
| 39 | Surface electronic properties of In-rich InGaN alloys grown by MOCVD. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 662-665. | 0.8 | 4 |
| 40 | Characterization of bimetallic Au-Pt(111) surfaces. Thin Solid Films, 2010, 518, 3650-3657. | 1.8 | 10 |
| 41 | Surface, bulk, and interface electronic properties of nonpolar InN. Applied Physics Letters, 2010, 97, . | 3.3 | 30 |